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Notice of Allowability	Application No.	Applicant(s)
	10/520,099	HOSHI ET AL.
	Examiner	Art Unit
	Felisa C. Hiteshew	1722
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGOT THE OFFICE OF THE OFFICE OF	(OR REMAINS) CLOSED in this appoint of the communication GHTS. This application is subject to	plication. If not included will be mailed in due course, THIS
1. This communication is responsive to the amendment filed of	on August 24, 2006.	
2. The allowed claim(s) is/are <u>12-40</u> .		
 3.	been received. been received in Application No cuments have been received in this in of this communication to file a reply of ENT of this application. Itted. Note the attached EXAMINER's reason(s) why the oath or declarate be submitted. On's Patent Drawing Review (PTO-S Amendment / Comment or in the Office of BIOLOGICAL MATERIAL in oit of BIOLOGICAL MATERIAL in	complying with the requirements S AMENDMENT or NOTICE OF tion is deficient. 948) attached office action of the back) of the complying with the requirements.
Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	5. Notice of Informal Page 1 Notice of Informal Page 1 No./Mail Date 2 No./Mail Date 3. Examiner's Amendma 8. Examiner's Stateme 9. Other	(PTO-413), e

Application/Control Number: 10/520,099

Art Unit: 1722

Allowable Subject Matter

Page 2

- 1. Claims 12-40 are allowed.
- 2. The following is an examiner's statement of reasons for allowance: The most relevant prior art of reference was the art submitted by the applicants. However, they do not teach nor fairly suggest singularly or in any combination thereof a method for producing a silicon wafer for epitaxial growth wherein a silicon wafer for epitaxial growth is produced by growing a silicon single crystal with doping nitrogen according to the CZ method, with controlling F/G (mm2/min x K) in the range of 0.30 or more where F (mm/min) is a rage of crystal growth and G (K/mm) is a temperature gradient near growth interface when the silicon single crystal is grown, and with controlling a passage time (min) at 1150 to 1050*C in the range of 40 minutes or more, in the region wherein at least the center of the wafer becomes V region in which the void defects are generated, and then slicing the grown silicon single crystal.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the Examiner should be directed to Felisa Hiteshew whose telephone number is (571) 272-1463. The examiner can normally be reached on Mondays through Thursday from 5:30 AM to 4:00 PM with Fridays off.

If attempts to reach the examiner by telephone are unsuccessful, the

Application/Control Number: 10/520,099

Art Unit: 1722

examiner's supervisor, Yogendra Gupta, can be reached on (571) 272-1316. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-1463.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system. see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Page 3